■ Joh Information

Department Study on group III nitride semiconductors for novel photonic devices	■ Job Information		
Department Advanced ICT Research Institute / Kobe Frontier Research Center, DUV ICT Device Laboratory Work Contents (Research theme) Study on group III nitride semiconductors for novel photonic devices Main research is design, crystal growth, device fabrication, and characterization of AlGaN-based deep ultraviolet (DUV) light-emitting and/or DUV laser diodes using MOCVD techniques. The Article 15(2) of the Act on the activation of Science, Technology and Innovation will be applied to this work content. Employees to be hired through this recruitment may apply for external coapetitive research fundings such as Grant-in-id for Scientific Research (SMEMI) and NCT's internal research fundings. Application requirement Application MOCVD techniques or fabrication of light-emitting diodes will be preferred. Application for people on the employment period in case of fully renewing NB. Contract could be renewed. The employment period in case of fully renewing the profession of the profes	Subject No.	2026R-33	
Work Contents (Research theme)	Job Title	Fixed Term Researcher	
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Applicants must have Ph.D. degree. Especially, applicants having experience of crystal growth of group III nitride semiconductors using MOCVD techniques or fabrication of light-emitting diodes will be preferred. Recruiting (Number of people) Contract period The employment period in case of fully renewing modes and the processing of the complex of			
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Up to 5 years if certain conditions are fulfilled Fig. 100 Salary (basic salary) Work Place Up to 5 years if certain conditions are fulfilled Fig. 100 Separate (special conditions) Fig. 100 Separate (s	Contract period	N.B. Contract could be renewed.	
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Working frequency 5days/week (7.5hours/day)	Work Place	L. The state of th	
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^{*} Scope of change in work and workplace: No changes are expected in general

* The expressions used in "Work Contents (Research theme)" and "Detail of Work Contents" and the names of
"Department" and "Work Place" may be subject to change due to organizational restructuring or other reasons.